## **Program: BE Biomedical Engineering Curriculum Scheme: Revised 2016**

## **Examination: Final Year Semester VIII**

Course Code: BMC801 and Course Name: Biomedical Microsystems Time: 1 hour Max Marks:50

- 1 Type of silicon wafers are
- (a) n-type, p-type
- (b) S-type, n-type
- (c) a-type, b-type
- (d) c-type, z-type
- 2 Silicon Wafers are of the shape
- (a) Hexagonal
- (b) Rectangle
- (c) Circle
- (d) Square
- 3 A change in electrical resistance of solids when subjected to stress is known as
- (a) piezoelectricity
- (b) piezocrystal
- (c) piezocapacitance
- (d) piezoresistance
- 4 Silicon wafer is made up of
- (a) silicon nitride
- (b) silicon dioxide
- (c) pure silicon
- (d) silicon monoxide
- 5 Dopant used for polyphenylene sulfide is
- (a) HCI
- (b) NaCl
- (c) AsF5
- (d) H2O
- 6 ULPA filter is
- (a) Ultra Light Particulate Air
- (b) Ultra Light Particle Air
- (c) Ultra Low Particulate Air
- (d) Ultra Low Pressure Air
- 7 Which of the following is a MEMs device or component?
- (a) Micro gear
- (b) inductor
- (c) microscope
- (d) transformer
- 8 Common p-type dopant for silicon is
- (a) boron
- (b) phosphorus
- (c) arsenic
- (d) antimony
- 9 Micromotors are most commonly produced by
- (a) etching
- (b) AFM
- (c) LIGA process
- (d) CVD
- 10 Toxic gases such as CO, CO2, NO, O3 can be detected using
- (a) Pressure sensor
- (b) Thermal sensor
- (c) Chemical sensor
- (d) Optical sensor
- 11 Smaller systems tend to move more quickly than larger systems because of
- (a) smaller displacement
- (b) lower inertia of mass
- (c) less workdone
- (d) higher frequencies associated
- 12 In MEMs Silicon nitride is used as
- (a) lens
- (b) actuator
- (c) Insulator

(d)	sensor
13	Select the appropriate material for wafer
(a)	Silicon
(b)	Pure gold
(c)	Platinum
(d)	Aluminium
14	Silicon wafer orientation is defined by the
(a)	quality
(b)	Miller index
(c)	packing material
(d)	type of silicon used
15	Equal amount of gallium and arsenic atoms
(a)	makes a metal
(b)	makes a liquid
(c)	makes gallium arsenide
(d)	is not a good substrate
16	Which of the following material is used in MEMs for its optical property
(a)	silicon
(b)	argon PDMS
(c) (d)	helium
(u) 17	HEPA filters are used in
(a)	clean room
(b)	air dryer
(c)	water purifier
	HCI filtering
18	Wafers are produced by slicing
(a)	condiments
(b)	glass
(c)	Silicon cylindrical ingots
(d)	Sand
19	Silicon is as light as
(a)	Aluminium
(b)	gold
(c)	iron
(d)	steel
20	Silicon has same Young's modulus as
(a)	Aluminium
(b)	gold
(c)	iron
	steel
21	Silicon wafer orientation is defined by the
(a)	quality Miller index
(b)	
(c) (d)	packing material type of silicon used
22	As per scaling law in electricity current and length possesses following relation
(a)	inverse
(b)	cube
(c)	square
(d)	square root
23	is an optical technique used for determination of the dielectric properties of thin films
(a)	AFM
(b)	TEM
(c)	SEM
(d)	Ellipsometer
24	In, transmitted electrons are involved to view thin specimens
(a)	TEM
(b)	Profilometer
(c)	Ellipsometer
(d)	AFM
25	is a resist used in electron beam lithography
(a)	PDMS
(b)	conducting polymer
(q)	polyaniline PMMA
(d)	LIMING

26	Typical spin speed of photoresists depends on
(a)	velocity
(b)	viscosity
	intensity
(d)	pressure
27	dry etching involves the creation of
(a)	plasma
(b)	SiO2
(c) (d)	photoresist metal
(u) 28	RIE stands for
(a)	Resonative ion etching
(b)	Reactive ion etching
(c)	Reaction ion etching
(d)	Reflective ion etching
29	Role of photosensitive film is to produce on substrate
(a)	coating
(b)	pattern
(c)	defects
(d)	etching
30	The most popular light source for photolithography
(a)	mercury vapour lamp
(b)	LCD
(c)	incandescent lamp
(d)	LED The west stelling to sharing a
31	The wet etching technique
(a) (b)	removes unmasked area removes masked area
٠,	add material on masked area
(d)	add material on unmasked area
32	technique is based on the emission of secondary electrons from the surface of a specimen
(a)	AFM
(b)	SEM
	•
(c)	Profilometer
(c) (d)	Profilometer Ellipsometer
(d)	Ellipsometer
(d) 33	Ellipsometer DRIE stands for
(d) 33 (a) (b) (c)	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching
(d) 33 (a) (b) (c) (d)	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching deep reflective ion etching
(d) 33 (a) (b) (c) (d) 34	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching deep reflective ion etching Common light sources used in photolithography have wavelength in range
(d) 33 (a) (b) (c) (d) 34 (a)	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching deep reflective ion etching Common light sources used in photolithography have wavelength in range 100 - 250 nm
(d) 33 (a) (b) (c) (d) 34 (a) (b)	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching deep reflective ion etching Common light sources used in photolithography have wavelength in range 100 - 250 nm 300 - 500 nm
(d) 33 (a) (b) (c) (d) 34 (a) (b) (c)	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching deep reflective ion etching Common light sources used in photolithography have wavelength in range 100 - 250 nm 300 - 500 nm 500 - 700 nm
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(d) 33 (a) (b) (c) (d) 34 (a) (b) (c) (d) 35 (a)	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching deep reflective ion etching Common light sources used in photolithography have wavelength in range 100 - 250 nm 300 - 500 nm 500 - 700 nm 850 - 1000 nm lon implantation is implanting foreign substances by slow diffusion
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(d) 33 (a) (b) (c) (d) 34 (a) (b) (c) (d) 35 (a) (b) (c) (d) 36 (a) (b) (c) (d) 37 (a) (b)	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching deep reflective ion etching Common light sources used in photolithography have wavelength in range 100 - 250 nm 300 - 500 nm 500 - 700 nm 850 - 1000 nm Ion implantation is implanting foreign substances by slow diffusion melting insertion by force diffusion RCA is used for the cleaning substrate Glass PMMA Silicon PDMS Following deposition methods used for Silicon dioxide Spinning Spray
(d) 33 (a) (b) (c) (d) 34 (a) (b) (c) (d) 35 (a) (b) (c) (d) 36 (a) (b) (c) (d) 37 (a) (b) (c)	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching deep reflective ion etching Common light sources used in photolithography have wavelength in range 100 - 250 nm 300 - 500 nm 500 - 700 nm 850 - 1000 nm lon implantation is implanting foreign substances by slow diffusion melting insertion by force diffusion RCA is used for the cleaning substrate Glass PMMA Silicon PDMS Following deposition methods used for Silicon dioxide Spinning Spray Wet Oxidation
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(d) 33 (a) (b) (c) (d) 34 (a) (b) (c) (d) 35 (a) (b) (c) (d) 36 (a) (b) (c) (d) 37 (a) (b) (c) (d) 38	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching deep reflective ion etching Common light sources used in photolithography have wavelength in range 100 - 250 nm 300 - 500 nm 500 - 700 nm 850 - 1000 nm Ion implantation is implanting foreign substances by slow diffusion melting insertion by force diffusion  RCA is used for the cleaning substrate Glass PMMA Silicon PDMS Following deposition methods used for Silicon dioxide Spinning Spray Wet Oxidation Electroplating Thermal Deposition is popular for the following material
(d) 33 (a) (b) (c) (d) 34 (a) (b) (c) (d) 35 (a) (b) (c) (d) 36 (a) (b) (c) (d) 37 (a) (b) (c) (d) 38 (a)	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching Common light sources used in photolithography have wavelength in range 100 - 250 nm 300 - 500 nm 500 - 700 nm 850 - 1000 nm Ion implantation is implanting foreign substances by slow diffusion melting insertion by force diffusion RCA is used for the cleaning substrate Glass PMMA Silicon PDMS Following deposition methods used for Silicon dioxide Spinning Spray Wet Oxidation Electroplating Thermal Deposition is popular for the following material Polymers
(d) 33 (a) (b) (c) (d) 34 (a) (b) (c) (d) 35 (a) (b) (c) (d) 36 (a) (b) (c) (d) 37 (a) (b) (c) (d) 38 (a) (b) (c) (d) 38 (a) (b)	Ellipsometer  DRIE stands for deep reactive ion etching diode reactive ion etching deep regenerative ion etching deep reflective ion etching Common light sources used in photolithography have wavelength in range 100 - 250 nm 300 - 500 nm 500 - 700 nm 850 - 1000 nm Ion implantation is implanting foreign substances by slow diffusion melting insertion by force diffusion  RCA is used for the cleaning substrate Glass PMMA Silicon PDMS Following deposition methods used for Silicon dioxide Spinning Spray Wet Oxidation Electroplating Thermal Deposition is popular for the following material

39 Select the appropriate technique for coating of polymers

(a)	Spin coating
(b)	Chemical Vapour Depositing
(c)	Physical Vapour Depositing
(d)	Electroplating
40	Following is a type of chemical vapour deposition
(a)	Electroplating
(b)	Evaporation
(c)	LPCVD
(d)	PVD
41	What is the evaporation temperature of copper in degree Celsius?
(a)	200
(b)	1516
(c)	0
(d)	25
42	Following doping can be carried out at lower temperature
(a)	spraying
(b)	oxidation
(c)	ion implantation
(d)	diffusion
43	In MEMs fabrication, following type of water is used
(a)	tap water
(b)	filtered water
(c)	salted water
(d)	DI water
44	In MEMs fabrication, following is a critical environmental parameter for patterning submicron devices
(a)	size of the dust particle
(b)	size of silicon wafer
(c)	type of silicon wafer size of the room
(d)	
45 (a)	In photolithography, sensitivity of resist depends on shape of substrate
(a) (b)	size of substrate
(c)	type of substrate
(d)	wavelength of light
(u) 46	In which technique of deposition step coverage is poor
(a)	Evaporation
(b)	DC sputter
(c)	RF sputter
(d)	PECVD
47	Which of the following deposition technique grain size is minimum
(a)	Thermal Evaporation
(b)	Sputtering
(c)	electron beam evaporation
(d)	Electroplating
48	Which of the following deposition technique uses electrochemical reaction
(a)	evaporation
(b)	electroplating
(c)	PECVD
(d)	Sputtering
49	Followings is a dielectric layer deposition techniques
(a)	Spin coating
(b)	Electrolessplating
(c)	Chemical Vapour Deposition
(d)	Electroplating
50	One of the major problems of surface micromachining is
(a)	Absorption
	Adhesion of layers
(c)	Epitaxy
(d)	Evaporation  Sociificial layer is an essential component in
51 (a)	Sacrificial layer is an essential component in
(a) (b)	Bulk micromachining LIGA
(b)	Surface micromachining
(c) (d)	wet etching
(u) 52	lithography technique can pattern nonplanar substrate, unusual materials and large areas
	X- ray

(b)	Photo
(c)	soft
(d)	electron beam
53	is a common metal used in the process steps of LIGA.
(a)	Nickel
(b)	Aluminium
(c)	Steel
(d)	Cobalt
54	Micro-contact Printing is a technique related to
(a)	photolithography
(b)	electron beam lithography
(c)	X- ray lithography
(d)	soft lithography
55 (a)	Stamp, mold, or mask having relief structures on its surface is the key element of
(a)	X- ray lithography
(b) (c)	soft lithography photolithography
(d)	electron beam lithography
56	Lithography, Electroforming, molding are essential steps of
(a)	Bulk micromachining
(b)	LIGA
(c)	Surface micromachining
(d)	Evaporation
57	Select appropriate material for substrate in LIGA
(a)	Glass with thin metal layer
(b)	Glass
(c)	Dielectric
(d)	polymer
58	Replica molding can be used in
(a)	photolithography
(b)	electron beam lithography
(c)	X- ray lithography
(d)	soft lithography
59	μTAS systems comprised of
(a)	only result analysis
(b)	a sampling unit, a microfluidic unit, a detector system and an electronic controller
(c)	only separation and detection of samples
(d)	only sample analysis
60	In μTAS, separation methods used
(a)	Titration Capillary electrophorosis
(b)	Capillary electrophoresis Sedimentation
(c) (d)	Centrifugation
(u) 61	Detection technique used in μTAS is
(a)	Fluorescence
(b)	Dielectrophoresis
(c)	Electrophoresis
(d)	Chromatography
62	What is the full form of µTAS?
(a)	Mini Thermal Analytical System
(b)	Micro Total Analysis System
(c)	Micro Transfer Analytical System
(d)	Micro Total Analytics Signal
63	In thermal microactuator, change in length depends on
(a)	temperature
(b)	flow
(c)	width of channel
(d)	size of channel
64	In electroosmotic flow, direction of flow depends on
(a)	concentration of ion
(b)	DC supply polarity
(c)	particle size
(d)	frequency of supply
65 (a)	In μTAS, following technique does not require charged particle Electro osmosis
(4)	Licon o obinosis

(b) electrophoresis

(c)	Dielectrophoresis
(d)	capillary
66	In microsyringe pump, dispense capacity depends on
(a)	displacement of stem
(b)	material of stem
(c)	diameter of stem
(d)	shape of stem
67 (a)	In μTAS, micro channels is made up of
(a)	silver
(b)	gold
(c)	PDMS
(d)	fluoride
68	The sampling subsystem should contain a micro filter consists of
(a)	filter paper
(b)	conventional polymer membrane
(c)	metal filter
٠,	muslin cloth
69	The immobilization of bioreceptor is achieved by
(a)	Assimilation
	Adsorption
(c)	Adhesion
٠,	cohesion
70	Which of the following is present in glucose biosensors
(a)	amino acids
(b)	glucose oxidase
(c)	nucleic acid
(d)	galactose
71	In case of Biosensors, can be a biorecognition element
(a)	Oxide
(b)	Enzyme
(c)	metals
(d)	ceramics
72	Which of these biosensors use the principle of heat released or absorbed by a reaction
(a)	Potentiometric biosensor
(b)	Optical biosensors
(c)	Piezo-electric biosensors
(d)	Calorimetric biosensors
73	In glucose biosensor, a measure of change in is a measure of the glucose value.
(a)	carbons dioxide
(b)	oxygen
(c)	nitrogen
(d)	
74	ammonia
	ammonia Following acts as detector in Optical sensor
(a)	
(a) (b)	Following acts as detector in Optical sensor
	Following acts as detector in Optical sensor Light emitting diode
(b)	Following acts as detector in Optical sensor Light emitting diode Transistor
(b) (c)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe
(b) (c) (d)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode
(b) (c) (d) 75	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized
(b) (c) (d) 75 (a)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes
(b) (c) (d) 75 (a) (b)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose
(b) (c) (d) 75 (a) (b) (c)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea
(b) (c) (d) 75 (a) (b) (c) (d)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea Urease
(b) (c) (d) 75 (a) (b) (c) (d) 76	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea Urease Nanoparticles that are used as drug delivery systems are called as
(b) (c) (d) 75 (a) (b) (c) (d) 76 (a)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea Urease Nanoparticles that are used as drug delivery systems are called as nanocarriers
(b) (c) (d) 75 (a) (b) (c) (d) 76 (a) (b)	Following acts as detector in Optical sensor  Light emitting diode  Transistor  light pipe  Photo diode  For microencapsulation of bioreceptor can be utilized  liposomes  glucose  Urea  Urease  Nanoparticles that are used as drug delivery systems are called as nanocarriers  nanotubes
(b) (c) (d) 75 (a) (b) (c) (d) 76 (a) (b) (c)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea Urease Nanoparticles that are used as drug delivery systems are called as nanocarriers nanotubes nanosensors
(b) (c) (d) 75 (a) (b) (c) (d) 76 (a) (b) (c) (d)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea Urease Nanoparticles that are used as drug delivery systems are called as nanocarriers nanotubes nanosensors nanoarray
(b) (c) (d) 75 (a) (b) (c) (d) 76 (a) (b) (c) (d) 77	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea Urease Nanoparticles that are used as drug delivery systems are called as nanocarriers nanotubes nanosensors nanoarray A characteristic of DNA biosensors is
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(b) (c) (d) 75 (a) (b) (c) (d) 76 (a) (b) (c) (d) 77 (a) (b)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea Urease Nanoparticles that are used as drug delivery systems are called as nanocarriers nanotubes nanosensors nanoarray A characteristic of DNA biosensors is formation of DNA recognition layer detection of the change in light absorption
(b) (c) (d) 75 (a) (b) (c) (d) 76 (a) (b) (c) (d) 77 (a) (b) (c)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea Urease Nanoparticles that are used as drug delivery systems are called as nanocarriers nanotubes nanosensors nanoarray A characteristic of DNA biosensors is formation of DNA recognition layer detection of the change in light absorption detection of the photon out for luminescent
(b) (c) (d) 75 (a) (b) (c) (d) 76 (a) (b) (c) (d) 77 (a) (b) (c) (d)	Following acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea Urease Nanoparticles that are used as drug delivery systems are called as nanocarriers nanotubes nanosensors nanoarray A characteristic of DNA biosensors is formation of DNA recognition layer detection of the change in light absorption detection of the angle at which electrons are emitted
(b) (c) (d) 75 (a) (b) (c) (d) 76 (a) (b) (c) (d) 77 (a) (b) (c) (d) 78	Eollowing acts as detector in Optical sensor Light emitting diode Transistor light pipe Photo diode For microencapsulation of bioreceptor can be utilized liposomes glucose Urea Urease Nanoparticles that are used as drug delivery systems are called as nanocarriers nanotubes nanosensors nanoarray A characteristic of DNA biosensors is formation of DNA recognition layer detection of the change in light absorption detection of the angle at which electrons are emitted Coat and poke drug delivery approach is followed in

	Hollow microneedle
	In case of Biosensors, is the most important component.
	display metals
	ceramics
(d)	biorecognition element
	In biosensor, is the physico-chemical component
(a)	Enzymes
(b)	Anti-bodies Anti-bodies
(c)	Transducer
(d)	Cells or tissues
	What is an Analyte?
	Any molecule may be protein, toxin, antigen, etc.
	The concentration of the molecule
(c)	The component which should not be detected
	The component which gives background noise
62 (a)	Polymer membrane permeation is a type of intravenous drug delivery
	injection
	Transdermal drug delivery system
	Which of the following is a painful way of drug delivery?
	Topical cream
(b)	Transdermal patch
(c)	Hypodermic needle
(d)	Microneedle
84	The simplest amperometric biosensors for glucose detection involve
(a)	·
	Clark oxygen electrode
	Carbon dioxide electrode
	copper electrode
85 (a)	Magnetic bio sensor is widely used for Blood detection
(b)	DNA detection
(c)	particle detection
	photo detection
	The generation of ions by various chemical events that change the electrical properties of the analyte solution is detected.
	Ion Sensitive Biosensors
(b)	Colorimetric biosensors
(c)	Magnetic Biosensors
(d)	Electrochemical Biosensors
	' ' ' ' ' <del></del>
	dendrimers
. ,	liposomes
(c)	polymers GNP
(u) 88	Poke and patch drug delivery approach is seen in
(a)	
	Solid microneedle
(c)	Dissolving microneedle
	Hollow microneedle
89	Transdermal devices deliver the drug through the
(a)	Eye
(b)	nose
	mouth
	Skin
90	is Level 3 of microsystems packaging
(a)	Die Devise
(b)	Device System
	Card
(u) 91	levels of packaging are there in microsystems packaging
(a)	Three
	Two
(c)	One
(d)	Four

92 \_\_\_\_\_ level is Level 2 of microsystems packaging
(a) Die
(b) Device
(c) System
(d) Card
93 \_\_\_\_\_ levels of packaging are there in electronic systems packaging

(a)	Three
(b)	Two
(c)	One
(d)	Four
94	Sawing the wafer is related to
(a)	surface bonding
(b)	Wire bonding
(c)	sealing
(d)	die preparation
95	of microsystem component is challenging in microsystems packaging compared to microelectronics packaging
(a)	bonding
(b)	cutting
(c)	sawing
(d)	dicing
96	level is Level 1 of microsystems packaging
(a)	Die
(b)	Device
(c)	System
(d)	Card
	Wafer dicing means
	sawing the wafer
	printing the wafer
	implanting the wafer
(d)	surface bonding
98	In die bonding, are used for better die isolation
(a)	solder alloys
	epoxy resin
	silicon carbide
	silicon rubber
	Self assembled closed colloidal structures composed of lipid bilayers are called as
(a)	dendrimers
(b)	liposomes
	polymers
	GNP
	The packaging of MEMS or microsystems together with signal processing is known as
	lab on a chip
	lab on a computer
	lab on a silicon
(d)	lab in a chip